



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION

Generic Copy

19-Dec-2005

SUBJECT: ON Semiconductor Final Product/Process Change Notification #15185

TITLE: Final Notification for Wafer Capacity Addition for MOSAIC5 Technology – Group10

EFFECTIVE DATE: 19-Feb-2006

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

AFFECTED PRODUCT DIVISION(S): Analog Power Division

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Matt Kas <fft7yg@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Clarence Rebello <ffbwpn@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 60 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

DESCRIPTION AND PURPOSE:

This is the last Final PCN for the listed devices originally notified on IPCN 11335. ON Semiconductor is pleased to announce the Qualification and Process Certification of the COM1 wafer fabrication facility located in Phoenix, Arizona to manufacture MOSAIC5 Bipolar technology products. MOSAIC5 products were previously fabricated in the Motorola MOS6 wafer fabrication facility in Mesa, Arizona.

The effective date of this change will be 60 days from the issuance of this PCN for the devices listed.

Device parameters will continue to meet Data Book specifications as detailed below. Reliability will continue to meet or exceed ON Semiconductor standards.

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In the course of reviewing the electrical data for the Group 10 released parts, the following changes will be made:

MC100EP16VA:

- Change VBB NECL Limits at All Temperatures to -1585 to -1385 mV (was -1550 to -1350 mV at -40°C, -1575 to -1375 mV at 25°C and -1600 to -1400 mV at 85°C).

MC100EP16VB:

- Change IEE Limits at -40°C to 25 to 45 mA
- Change IEE Limits at 25°C to 30 to 50 mA
- Change IEE Limits at 85°C to 32 to 52 mA
- Change VOH NECL Limits at 25 & 85°C to -1175 to -925 mV (was -1200 to -950 mV at 25°C and 85°C).
- Change VBB NECL Limits at All Temperatures to -1570 to -1340 mV (was -1540 to -1340 mV at -40°C, -1580 to -1380 mV at 25°C and -1610 to -1410 mV at 85°C).

MC100EP16VC:

- Change VOH NECL Limits at All Temperatures to -1175 to -925 mV (was -1195 to -945 mV at -40, 25°C and 85°C).
- Change VBB NECL Limits at All Temperatures to -1570 to -1340 mV (was -1575 to -1375 mV at -40°C, -1600 to -1400 mV at 25°C and -1625 to -1425 mV at 85°C).

Changes reflect typographical errors and Family Specifications, which match MOS6 devices. There were no changes to the actual design or function of the parts.

RELIABILITY DATA SUMMARY:**Reliability Test Results:**

Available

Contact your local ON Semiconductor Sales Office or Matt Kas

ELECTRICAL CHARACTERISTIC SUMMARY:

Electrical characteristic data available upon request. Electrical Performance has not changed.

CHANGED PART IDENTIFICATION:

Devices with date code of WW05, 2006 and forward may be manufactured in COM1.



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AFFECTED DEVICE LIST:

PART

**MCW100EP16VA
MC100EP16VAD
MC100EP16VADG
MC100EP16VADR2
MC100EP16VADR2G
MC100EP16VADT
MC100EP16VADTG
MC100EP16VADTR2
MC100EP16VADTR2G
MCW100EP16VB
MC100EP16VBD
MC100EP16VBDG
MC100EP16VBDR2
MC100EP16VBDR2G
MC100EP16VBDT
MC100EP16VBDTG
MC100EP16VBDTR2
MC100EP16VBDTR2G
MCW100EP16VC
MC100EP16VCD
MC100EP16VCDG
MC100EP16VCDR2
MC100EP16VCDR2G
MC100EP16VCDT
MC100EP16VCDTG
MC100EP16VCDTR2
MC100EP16VCDTR2G**